

NTE2426 (NPN) & NTE2427 (PNP) Silicon Complementary Transistors Darlington Switch

Description:

The NTE2426 and NTE2427 are silicon planer Darlington transistors in a SOT-89 type surface mount package designed for use in industrial switching applications such as print hammer, solenoid, relay, and lamp drivers.

Absolute Maximum Ratings:

Collector-Base Voltage (Open Emitter), V_{CBO}	90V
Collector-Emitter Voltage, V_{CER}	80V
Emitter-Base Voltage (Open Collector), V_{EBO}	5V
Collector Current, I_C	
Continuous	500mA
Peak	1.5A
Base Current, I_B	100mA
Total Power Dissipation ($T_A \leq +25^\circ\text{C}$, Note 1), P_{tot}	1W
Operating Junction Temperature (Note 2), T_J	+150°C
Storage Temperature Range, T_{stg}	-65° to +150°C
Thermal Resistance, Junction-to-Ambient (Note 1, Note 2), R_{thJA}	125K/W
Thermal Resistance, Junction-to-Tab (Note 2), R_{thJTAB}	10K/W

Note 1. Device mounted on a ceramic substrate; area = 2.5cm², thickness = 0.7mm.

Note 2. Based on maximum average junction temperature in line with common industrial practice.
 The resulting higher junction teperature of the output transistor part is taken into account.

Electrical Characteristics: ($T_J = +25^\circ\text{C}$ unles otherwise specified)

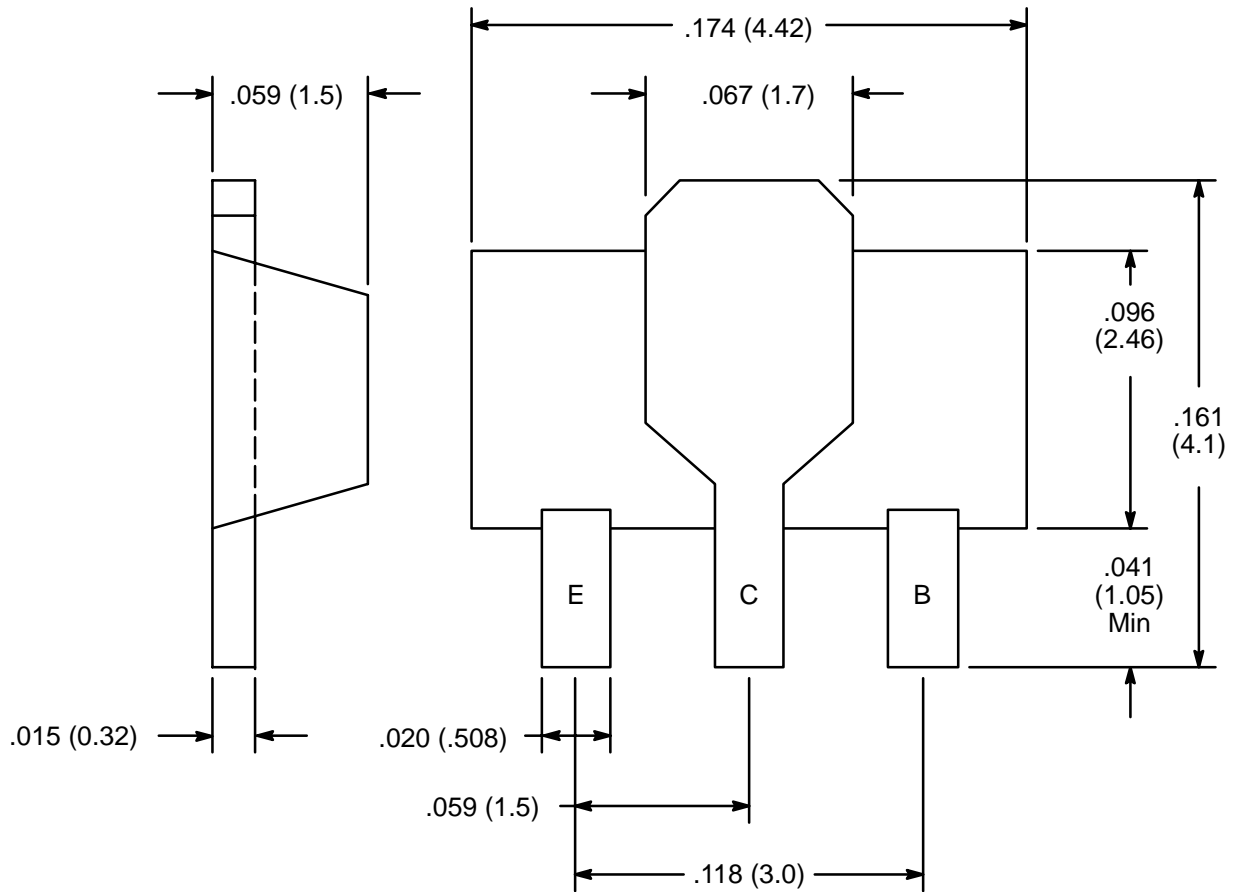
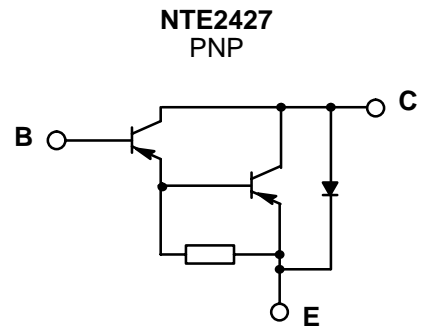
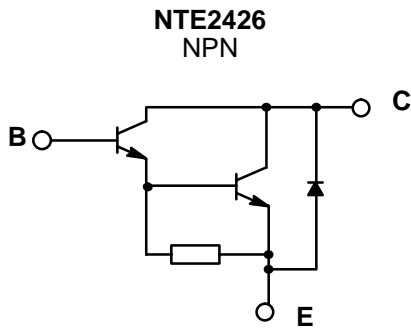
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CES}	$V_{CER} = 80V, V_{BE} = 0$	-	-	10	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 4V, I_C = 0$	-	-	10	μA
DC Current Gain	h_{FE}	$V_{CE} = 10V, I_C = 150mA$, Note 3	1000	-	-	
		$V_{CE} = 10V, I_C = 500mA$, Note 3	2000	-	-	

Note 3. Measured under pulsed conditions.

Electrical Characteristics (Cont'd): ($T_J = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 500\text{mA}, I_B = 0.5\text{mA}$	–	–	1.3	V
		$I_C = 500\text{mA}, I_B = 0.5\text{mA}, T_J = +150^\circ\text{C}$	–	–	1.3	V
Base–Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 500\text{mA}, I_B = 0.5\text{mA}$	–	–	1.9	V
Turn–On Time	t_{on}	$I_C = 500\text{mA}, I_{B(on)} = -I_{B(off)} = 0.5\text{mA}$	–	400	–	ns
Turn–Off Time	t_{off}		–	1500	–	ns

Schematic Diagram



Bottom View

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [Darlington Transistors](#) category:

Click to view products by [NTE manufacturer](#):

Other Similar products are found below :

[281287X](#) [SMMBT6427LT1G](#) [2N7371](#) [BDV64B](#) [JANTXV2N6287](#) [028710A](#) [SMMBTA64LT1G](#) [2N6350](#) [2SB1214-TL-E](#)
[SMMBTA14LT1G](#) [SBSP52T1G](#) [NJVMJD117T4G](#) [Jantx2N6058](#) [2N6353](#) [LB1205-L-E](#) [500-00005](#) [2N6053](#) [NJVMJD112G](#) [Jan2N6350](#)
[Jantx2N6352](#) [Jantx2N6350](#) [BULN2803LVS](#) [ULN2001N](#) [2SB1383](#) [2SB1560](#) [2SB852KT146B](#) [TIP112TU](#) [TIP122TU](#) [BCV27](#) [MMBTA13-](#)
[TP](#) [MMBTA14-TP](#) [MMSTA28T146](#) [BSP50H6327XTSA1](#) [KSH122TF](#) [NTE2557](#) [NJVNJD35N04T4G](#) [TIP115](#) [MPSA29-D26Z](#) [MJD127T4](#)
[FJB102TM](#) [BCV26E6327HTSA1](#) [BCV46E6327HTSA1](#) [BCV47E6327HTSA1](#) [BSP61H6327XTSA1](#) [BU941ZPFI](#) [2SB1316TL](#) [2SD1980TL](#)
[NTE2350](#) [NTE245](#) [NTE246](#)